OIPE IAP60 DEC 12 2006 PATENT & TRADEMARK OFFICE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Wu et al.

Attorney Docket No.: NOVLP091/NVLS-2889

Application No.: 10/820,525

Examiner: Maldonado, Julio J.

Filed: April 7, 2004

Group: 2823

Title: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on December 7, 2006 in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Signed: _____

Tara Hayden

INFORMATION DISCLOSURE STATEMENT BEFORE FINAL ACTION OR NOTICE OF ALLOWANCE (37 CFR §§ 1.56 AND 1.97(c))

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, a copy of which is attached, may be material to examination of the above-identified patent application. Applicants submit this reference in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make this citation of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that this reference indeed constitutes prior art.

This Information Disclosure Statement is being filed after the mailing date of the first Office Action on the merits, or after three months of the filing date of this application, whichever event occurred last, but it is believed before the mailing date of either: (i) a final action under §1.113 or (ii) a notice of allowance under §1.311, whichever occurs first.

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Accompanying this Information Disclosure Statement is

☐ a statement as specified in 37 CFR 1.97(e); or

☒ the fee set forth in 37 CFR 1.17(p).

If fees are due, enclosed is our Check No. 12604 for $180.00 in payment of the Information Disclosure Statement Fee. If it is determined that any additional fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP091).

Respectfully submitted,
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Form 1449 (Modified)	Atty Docket No.	Application No.:
	NOVLP091/NVLS-2889	10/820,525
Information Disclosure Statement By Applicant	Applicant: Wu et al.	
	Filing Date	Group
(Use Several Sheets if Necessary)	April 7, 2004	2823

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	7,094,713 B1	08.22.06	Niu et al.			
	A2	6,306,564	10.2001	Mullee, William H.			
	A3	2003/0066544 A1	04.2003	Jur et al.			
	A4	6,149,828 A	11.2000	Vaartstra, Brian A.			
	A5	6,943,121 B2	09.2005	Leu et al.			
	A6	2004/0102032 A1	05.2004	Kloster et al.			
	A7	2006/0197881	09.2006	Kang et al.			
	A8	6,331,480	12.2001	Tsai et al.			
	A9	4,968,384	11.1990	Asano, Akihiko			
	A10	5,648,175	07.1997	Russell et al.			
	A11	5,281,546	01.1994	Possin et al.			

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed September 8, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C2	U.S. Office Action mailed July 12, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
	C3	Wu et al., "Methods for Fabricating High Hardness/Modules Low Dielectric Constant Materials," Novellus Systems, Inc., Appln No. 11/369,658, filed March 6, 2006, pp. 1-33. [NOVLP148/NVLS-3111]
	C4	Dhas et al., "Method of Reducing Defects in PECVD TEOS Films," Novellus Systems, Inc., Appln No. 11/396,303, filed March 30, 2006, pp. 1-21. [NOVLP160/NVLS-3168]
	C5	U.S. Office Action mailed October 18,2006, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
	C6	Hoek et al., "VLSI Fabrication Processes for Introducing Pores Into Dielectric Materials," Novellus Systems, Inc., Appln No. Not yet assigned, Filed November 28, 2006, pages 1-35. [NOVLP100C1/NVLS-2956C1]

Examiner	Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.